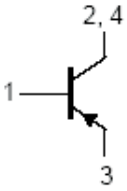
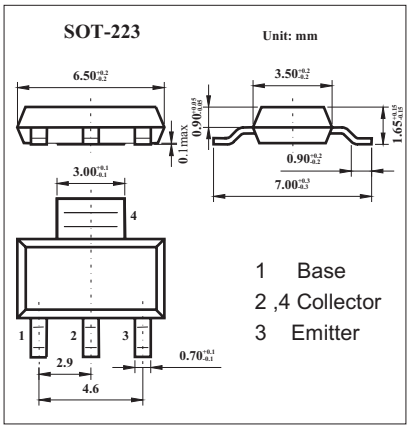
PNP medium power transistor
KCP69

Features

- High current (max. 1 A)
- Low voltage (max. 20 V).





Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	-32	V
Collector-emitter voltage	V_{CEO}	-20	V
Emitter-base voltage	V_{EBO}	-5	V
Collector current (DC)	I_C	-1	A
Peak collector current	I_{CM}	-2	A
Peak base current	I_{BM}	-200	mA
Total power dissipation $T_{amb} \leqslant 25$ ℃	P_D	1.35	W
Storage temperature	T_{stg}	-65 to +150	℃
Junction temperature	Tj	150	℃
Operating ambient temperature	T_{amb}	-65 to +150	℃
Thermal resistance from junction to ambient	$R_{th(j-a)}$	91	K/W
Thermal resistance from junction to solder point	$R_{th(j-s)}$	10	K/W

Electrical Characteristics Ta = 25℃

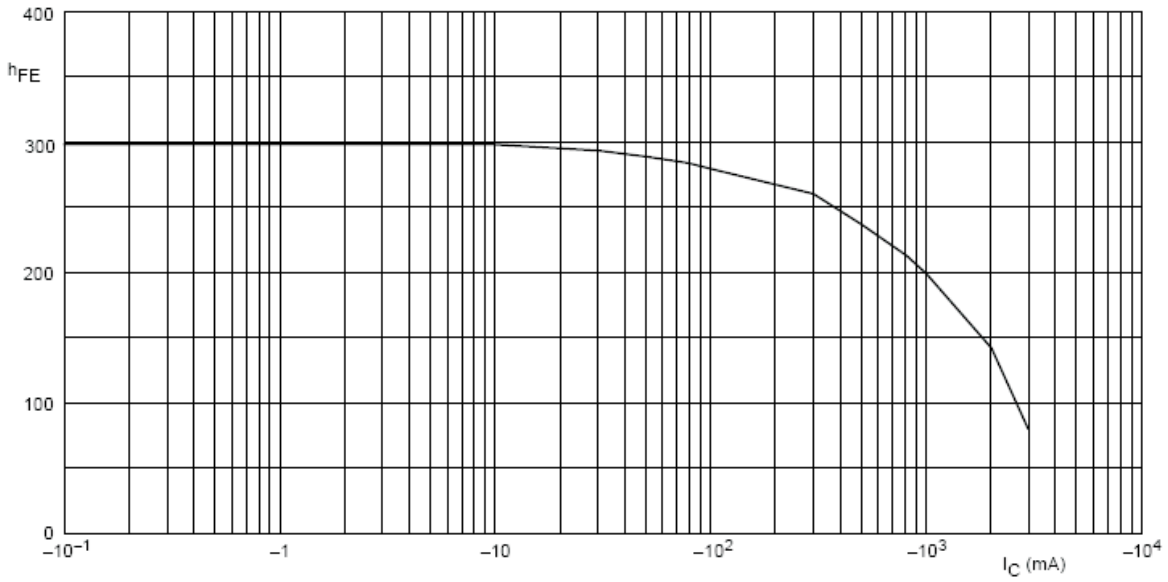
Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector cutoff current	I_{CBO}	I_E = 0 A; V_{CB} = -25 V			-100	nA
		I_E = 0 A; V_{CB} = -25 V; Tj = 150 ℃			-10	μA
Emitter cutoff current	I_{EBO}	I_C = 0 A; V_{EB} = -5 V			-100	nA
DC current gain	h_{FE}	V_{CE} = -10 V; I_C = -5 mA	50			
		V_{CE} = -1 V; I_C = -500 mA	85		375	
		V_{CE} = -1 V; I_C = -1 A	60			
DC current gain BCP69-16		V_{CE} = -1 V; I_C = -500 mA	100		250	
BCP69-25			160		375	
Collector-emitter saturation voltage	V_{CEsat}	I_C = -1 A; I_B = -100 mA;			-500	mV
Base-emitter voltage	V_{BE}	V_{CE} = -10 V; I_C = -5 mA		-620		mV
		V_{CE} = -1 V; I_C = -1 A			-1	V
Collector capacitance	C_c	I_E = ie = 0 A; V_{CB} = -5 V; f = 1 MHz		48		pF
Transition frequency	f_T	I_C = -10 mA; V_{CE} = -5 V; f = 100 MHz	40			MHz

Marking

Marking	BCP69

KCP69

■ Typlcal Characteristics



V_{CE} = −1 V.

Fig.1 DC current gain; typical values.